

ABSTRACT OF THE DISCLOSURE :

The present invention provides a novel photolithography processes using photoresist pattern having at least two areas
5 which has different thickness from each other for a fabrication method for a liquid crystal display device having reversed staggered and channel-etched type thin film transistors, reduce a number of photolithography processes required for whole of the fabrication process of the liquid crystal display
10 device, and improve brightness of the liquid crystal display device.